

ABSTRACT OF THE DISCLOSURE

In a magnetic random access memory for generating an inductive magnetic flux by passing current into write wirings disposed closely to MTJ elements, whose
5 resistance values varying depending on the magnetization array state of two magnetic layers of MTJ elements including two magnetic layers that hold a non-magnetic layer correspond to the stored information of "0"/"1", and writing information by varying the magnetization
10 direction of a free layer of the MTJ elements, the shape of the MT J elements is warped so as to coincide substantially with the magnetic field curve generated from the write wirings.